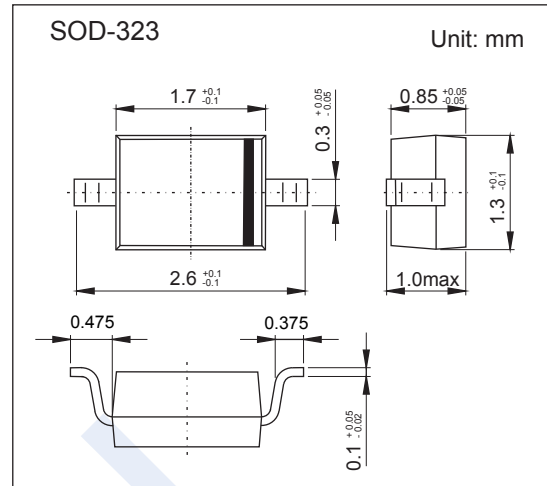


Rectifier Diodes

B0530WS

■ Features

- Very Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- High Conductance

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	30	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
RMS Reverse Voltage	V_R	21	
Average Rectified Output Current	I_o	0.5	A
Non-Repetitive Peak Forward Surge Current	I_{FSM}	2	
Power Dissipation	P_D	235	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	426	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-40to 125	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	$I_R = 500 \mu\text{A}$	30			V
Forward voltage	V_F	$I_F = 100 \text{ mA}$			0.36	
		$I_F = 500 \text{ mA}$			0.45	
Reverse voltage leakage current	I_R	$V_R = 15 \text{ V}$			80	μA
		$V_R = 20 \text{ V}$			100	
		$V_R = 30 \text{ V}$			500	
Junction capacitance	C_j	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$		60		pF

■ Marking

Marking	SE
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Rectifier Diodes B0530WS

■ Typical Characteristics

